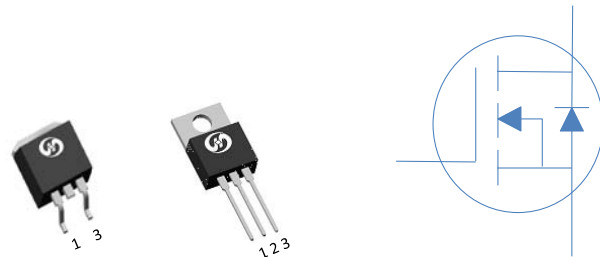


60V N-Ch Power MOSFET

V_{DS}		60	V
$R_{DS(on),typ}$	$V_{GS}=10V$	3.9	$m\Omega$
$R_{DS(on),typ}$	$V_{GS}=4.5V$	5.3	$m\Omega$
$R_{DS(on),typ}$	$V_{GS}=10V$	4.1	$m\Omega$
$R_{DS(on),typ}$	$V_{GS}=4.5V$	5.6	$m\Omega$
I_D (Silicon Limited)		105	A



Part Number	Package	Marking
HGB053N06SL	TO-263	GB053N06SL
HGP053N06SL	TO-220	GP053N06SL

Absolute Maximum Ratings at T_J

Parameter	Symbol	Conditions	Value	Unit
Continuous Drain Current (Silicon Limited)	I_D	T_C	105	A
		T_C	74	
Drain to Source Voltage	V_{DS}	-	60	V
Gate to Source Voltage	V_{GS}	-	± 20	V
Pulsed Drain Current	I_{DM}	-	250	A
Avalanche Energy, Single Pulse	E_{AS}	$L=0.4mH, T_C$	80	mJ
Power Dissipation	P_D	T_C	125	
Operating and Storage Temperature	T_J, T_{stg}	-	-55 to 175	

Absolute Maximum Ratings

Parameter	Symbol	Max	Unit
Thermal Resistance Junction-Ambient	$R_{\theta JA}$	46	
Thermal Resistance Junction-Case	$R_{\theta JC}$	1.2	

Electrical Characteristics at T_j

Static Characteristics

Parameter	Symbol	Conditions	Value			Unit
			min	typ	max	
Drain to Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	60	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	1.0	1.6	2.4	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS}=0V, V_{DS}=60V, T_j$	-	-	1	μA
		$V_{GS}=0V, V_{DS}=60V, T_j$	-	-	100	
Gate to Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
Drain to Source on Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=20A$ TO-263	-	3.9	5	$m\Omega$
		$V_{GS}=4.5V, I_D=20A$ TO-263	-	5.3	7.2	$m\Omega$
Drain to Source on Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=20A$ TO-220	-	4.1	5.3	$m\Omega$
		$V_{GS}=4.5V, I_D=20A$ TO-220	-	5.6	7.5	$m\Omega$
Transconductance	g	$V_{DS}=5V, I_D=20A$	-	48	-	S
Gate Resistance	R_G	$V_{GS}=0V, V_{DS}$	-	1.5	-	Ω

Dynamic Characteristics

Input Capacitance	C_{iss}		-	2274	-	pF
Output Capacitance	C_{oss}	$V_{GS}=0V, V_{DS}$	-	793	-	
	C_{rss}		-	35	-	
Total Gate Charge	$Q_g(10V)$	$V_{DD}=30V, I_D=20A, V_{GS}=10V$	-	36	-	nC
Total Gate Charge	$Q_g(4.5V)$		-	18	-	
Gate to Source Charge	Q_{gs}		-	4.5	-	
Gate to Drain (Miller) Charge	Q_{gd}		-	7.5	-	
Turn on Delay Time	$t_{d(on)}$	$V_{DD}=30V, I_D=20A, V_{GS}=10V,$ $R_G=10\Omega,$	-	11	-	ns
Rise time	t_r		-	7	-	
	t		-	35	-	
Fall Time	t		-	10	-	

Reverse Diode Characteristics

Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_F=20A$	-	0.9	1.2	V
Reverse Recovery Time	t_{rr}	$V_R=30V, I_F=20A, di_F$	-	30	-	ns
Reverse Recovery Charge	Q_{rr}		μs	-	53	-

Fig 1. Typical Output Characteristics

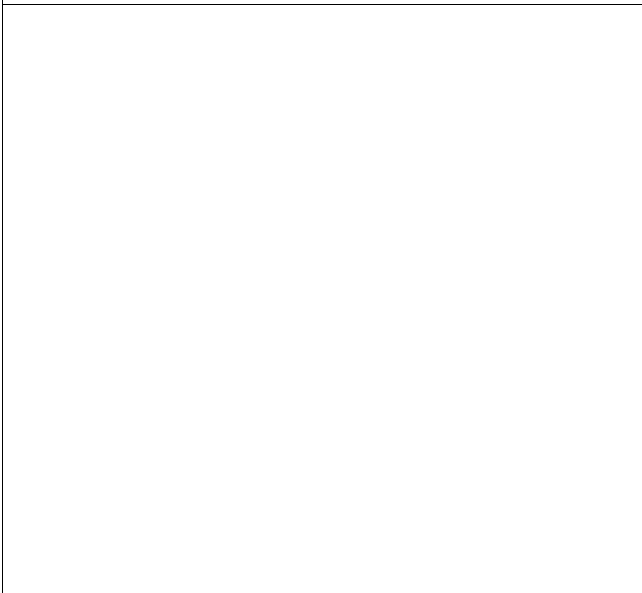


Figure 2. On-Resistance vs. Gate-Source Voltage

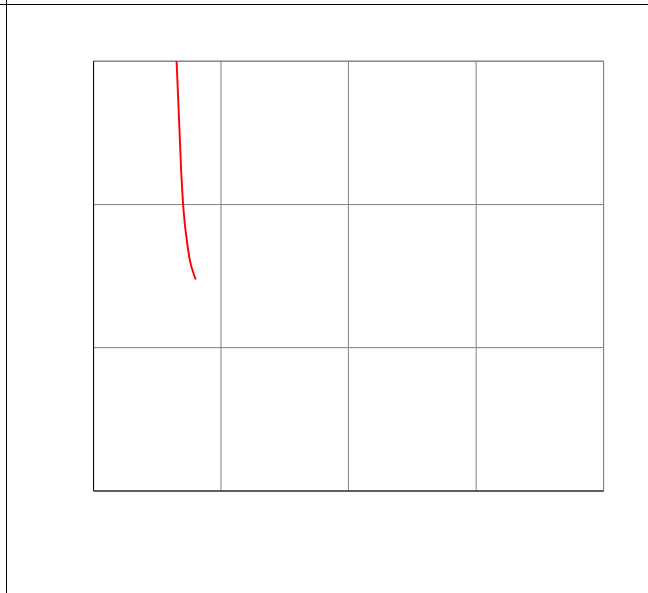


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

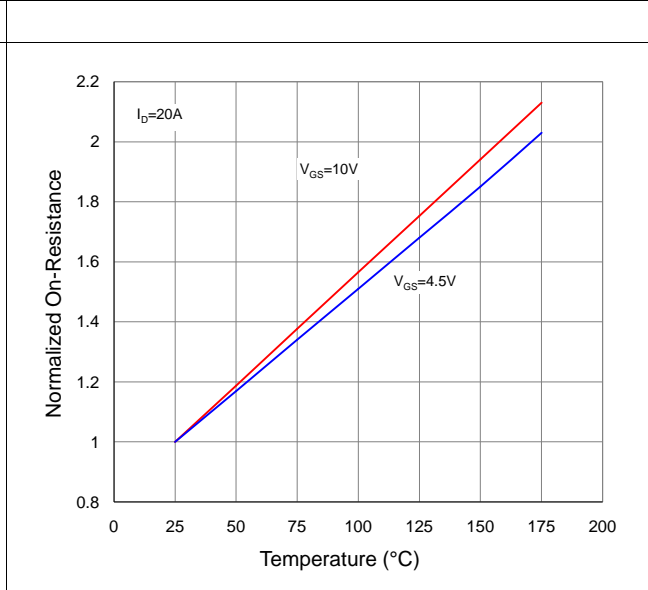
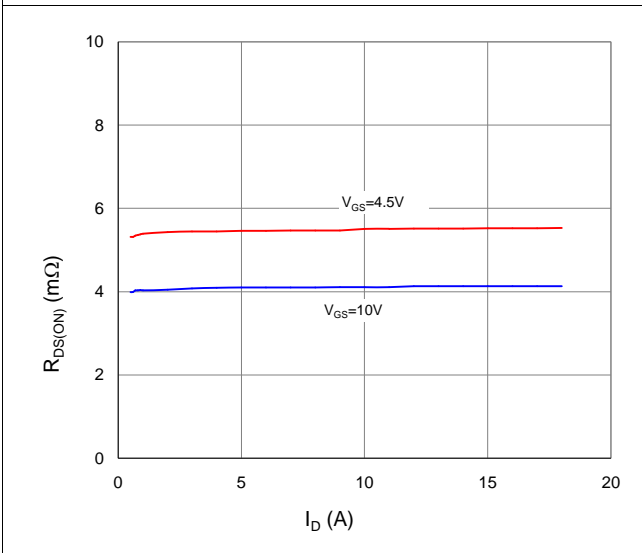


Figure 6. Typical Source-Drain Diode Forward Voltage

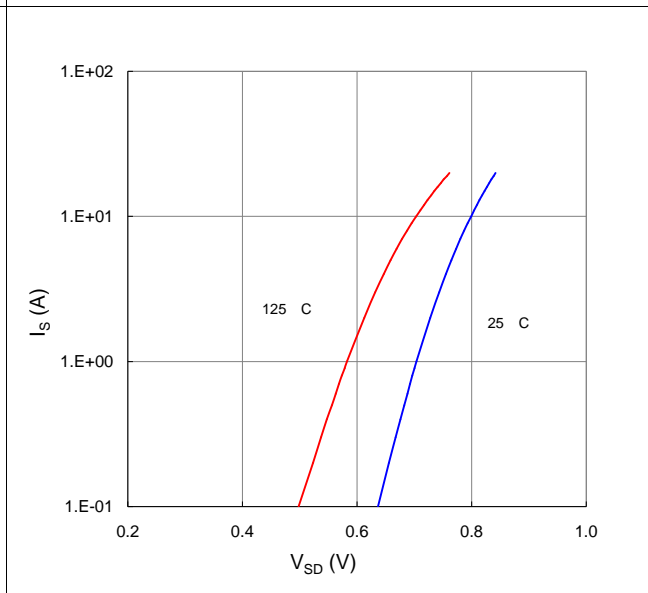
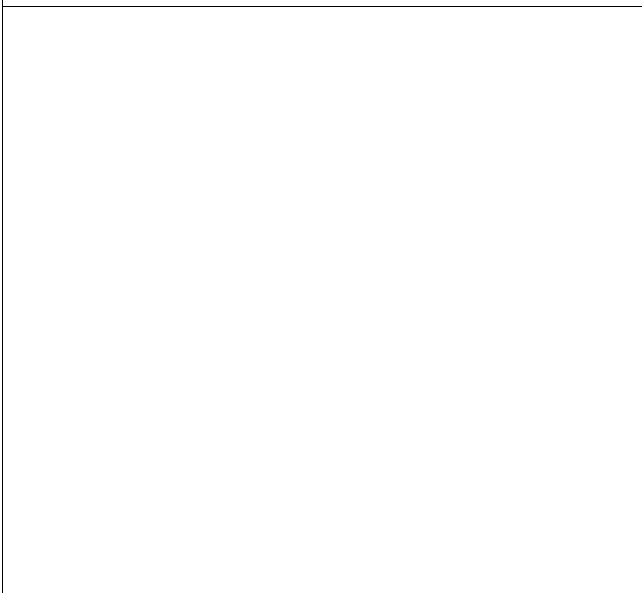


Figure 7. Typical Gate-Charge vs. Gate-to-Source Voltage

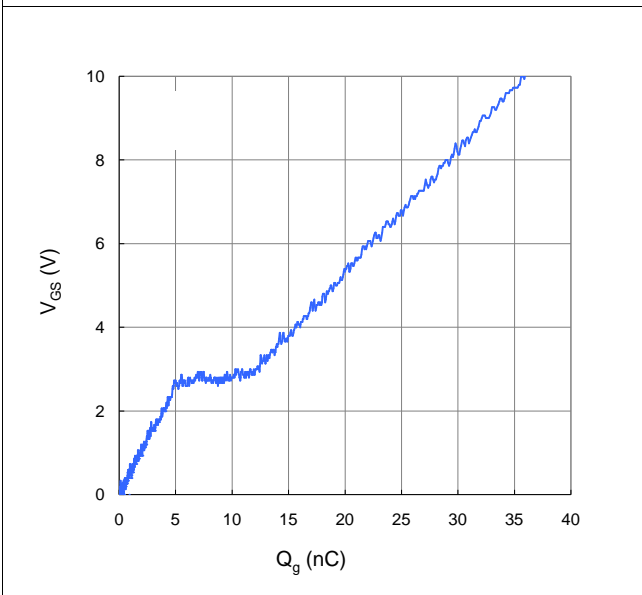


Figure 8. Typical Capacitance vs. Drain-to-Source Voltage

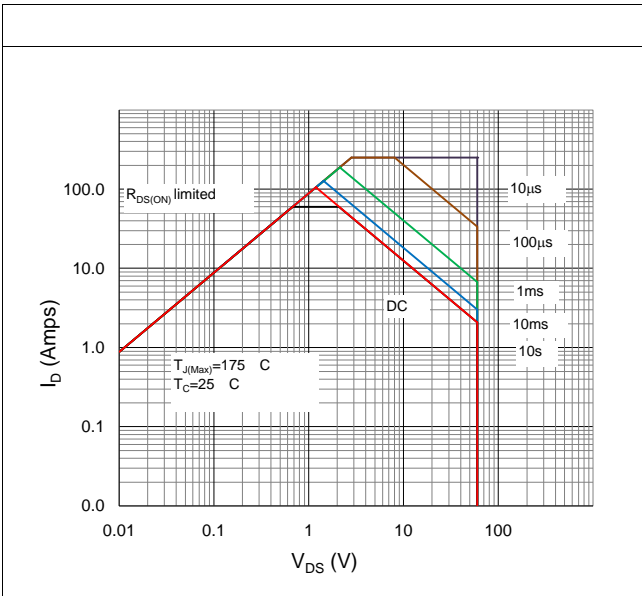
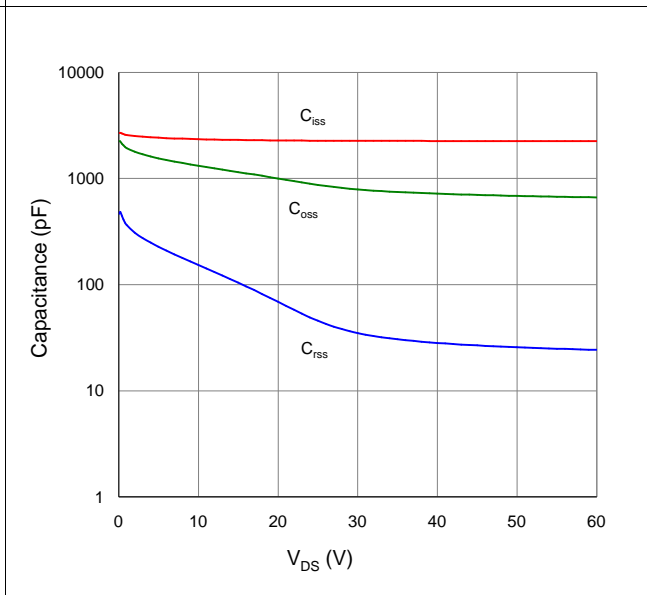
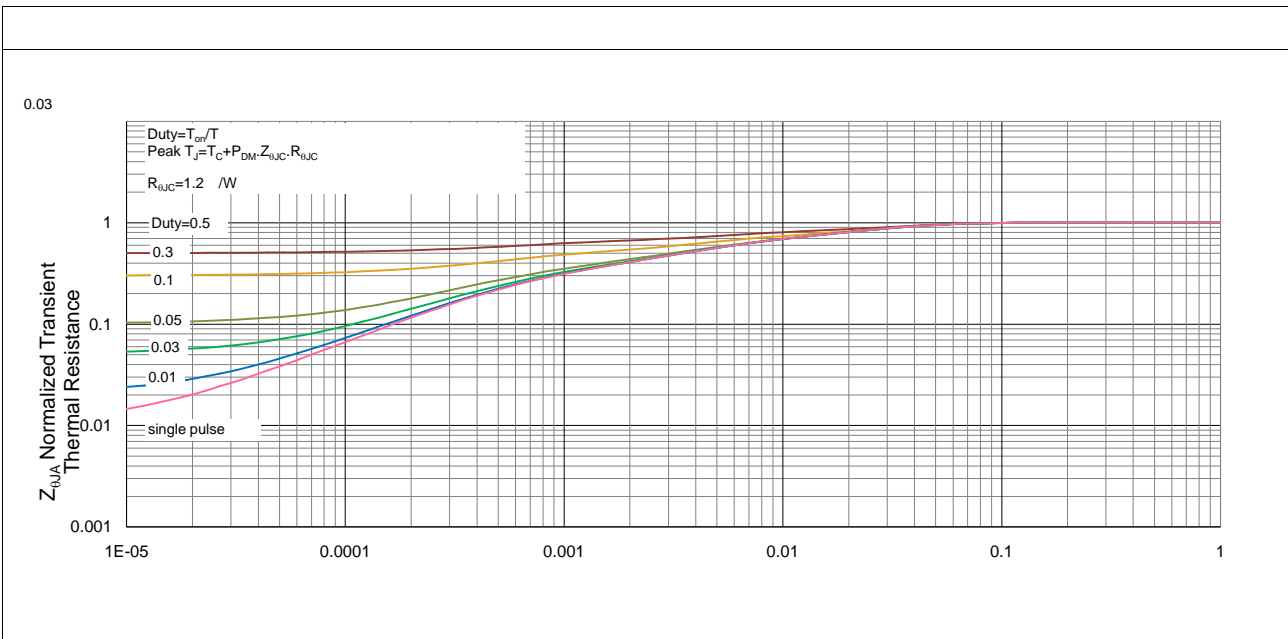
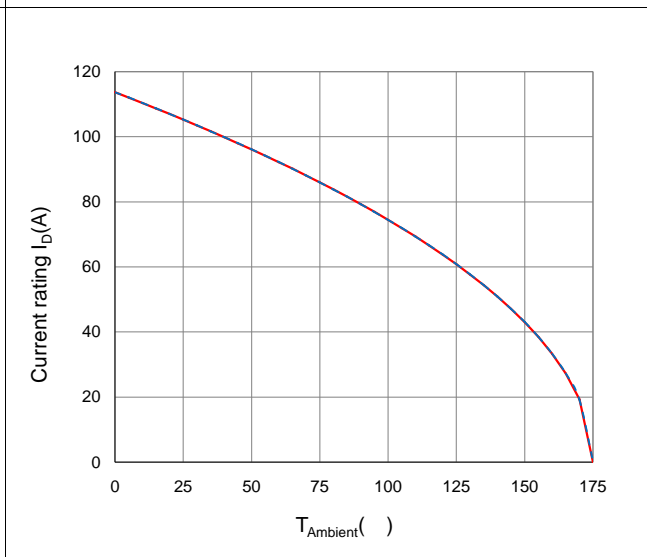


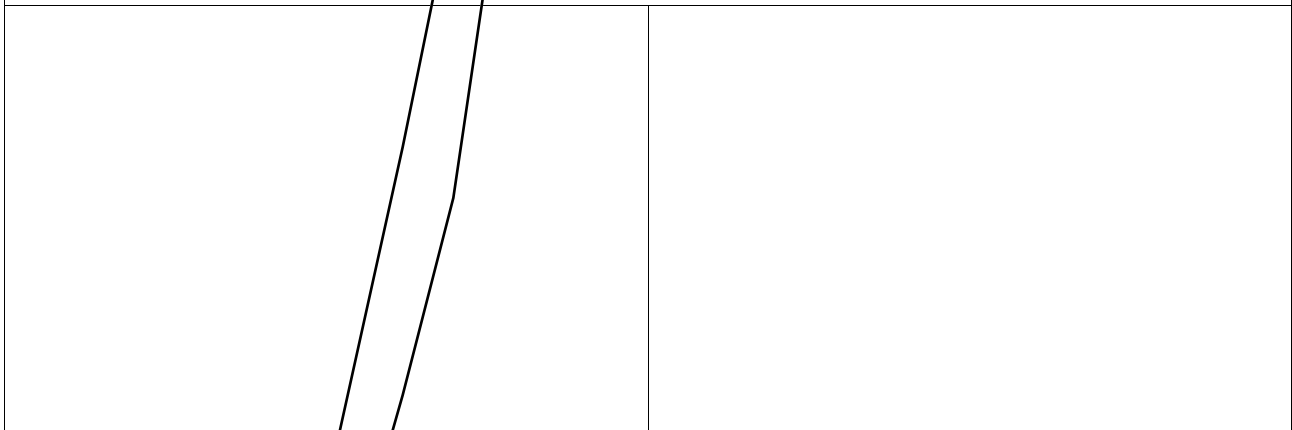
Figure 10. Maximum Drain Current vs. Case Temperature



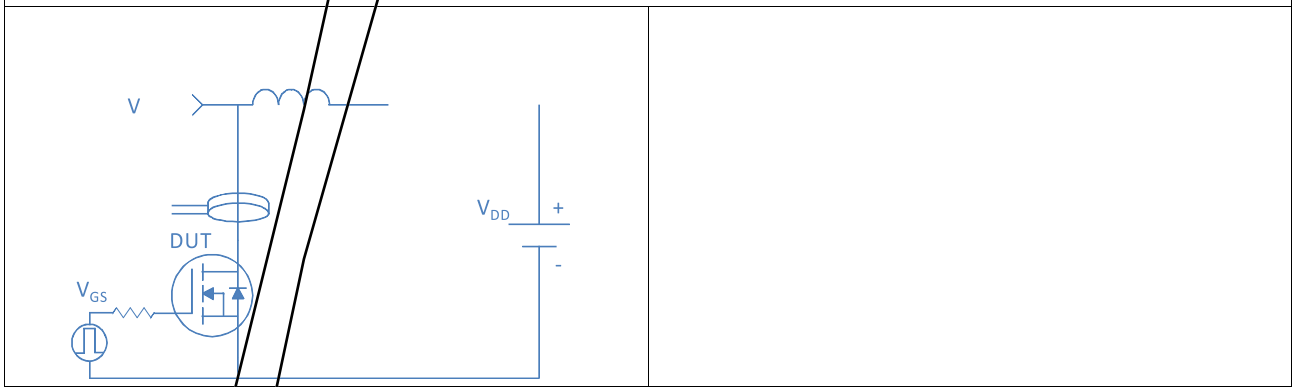
Inductive switching Test



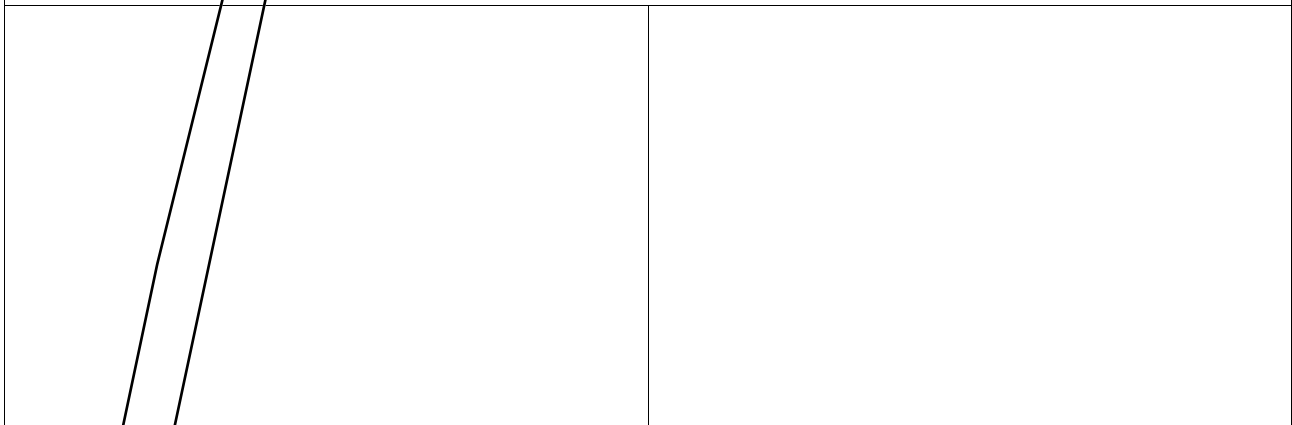
Gate Charge Test



Uclamped Inductive Switching (UIS) Test



Diode Recovery Test



		9.97	10.28
A2	9.80	10.00J	
D	4.30	4.50	4.70
E	9.00	9.20	9.40
G1	1.32	1.52	1.72
G2	0.70	0.82	0.95
G3	0.45	0.52	0.60
H	3.50	3.60	3.70
I	2.70	2.80	2.90
J	15.70	15.97	16.25
K	2.20	2.40	2.60
L	1.15	1.27	1.40
N	6.40	6.60	6.80

TO-263, 2 leads

Symbol	Min	Nom	Max
A	9.66	9.97	10.28
B	1.02	1.17	1.32
C	8.59	9.00	9.40
D1	1.14	1.27	1.40
D2	0.70	0.83	0.95
D3		5.08	
E	15.09	15.24	15.39
F	1.15	1.28	1.40
G	4.30	4.50	4.70
H	2.29	2.54	2.79
I		0.25	
K	1.30	1.45	1.60
a1	0.45	0.55	0.65
a2(degree)	0°		8°